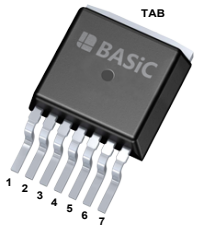
AB2M080120R

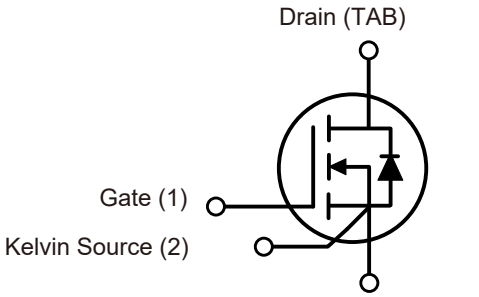
SiC MOSFET

Product Summary

V_{DS}	1200 V
I_D (T_C=25°C)	37 A
$R_{DS(on).typ}$	80 mΩ@V_{GS}=18V

Package: TO-263-7





Features

- Low On-Resistance with High Blocking Voltage
- Low Capacitance
- Avalanche Ruggedness
- Halogen Free, Rohs Compliant
- AEC−Q101 Qualified and PPAP Capable

Benefits

- High Frequency Operation
- Enabling Higher Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements

Applications

- On Board Charger(OBC)
- DC/DC Converter for EV/HEV
- Automotive Air-Conditioning Compressor
- Auxiliary drives

Package Pin Definitions

- TAB - Drain
- Pin1 - Gate
- Pin2 - Kelvin Source
- Pin3,4,5,6,7 - Power Source

Package Parameters

Part Number	Marking	Package
AB2M080120R	AB2M080120R	TO-263-7

Maximum Ratings

Symbol	Parameter	Test conditions	Value	Unit
V_{DSmax}	Drain-Source Voltage	V_{GS}=0V, I_D=100μA	1200	V
V_{GSmax} 1)	Gate-Source Voltage		-10/22	V
V_{GSop}	Recommend Gate-Source Voltage		-4/18	V
I_D	Continuous Drain Current	V_{GS}=18V, T_C=25°C	37	A
		V_{GS}=18V, T_C=100°C	26	A
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	68	A
P_{tot}	Power Dissipation	T_C=25°C, T_j=175°C	164	W
E_{AS}	Single pulse avalanche energy	T_C=25°C, L=2mH, I_{AS}=12.5A, V_{DD}=140V	156	mJ
T_j	Operating Junction Temperature		-55~175	°C
T_{stg}	Storage Temperature		-55~175	°C

1) Note: When using MOSFET Body Diode V_{GSmax}=-4/22V

Electrical Characteristics (Defined at T_j=25°C unless otherwise specified)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=100μA	1200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS}, I_D=5mA	2.3	2.7	3.5	V
		V_{GS}=V_{DS}, I_D=5mA,T_j=175°C		1.9		
I_{GSS}	Gate-Source Leakage Current	V_{GS}=18V, V_{DS}=0V			100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=1200V, V_{GS}=0V		1	50	μA
		V_{DS}=1200V, V_{GS}=0V,T_j=175°C		10	200	
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=18V, I_D=20A		80	100	mΩ
		V_{GS}=18V, I_D=20A,T_j=175°C		120		
		V_{GS}=15V, I_D=20A		105		
g_{fs}	Transconductance	V_{DS}=10V, I_D=20A		7.7		S

Thermal Characteritics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal Resistance from Junction to Case		0.91	1.20	K/W

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=800V f=1MHz, V_{AC}=25mV		1010		pF
C_{oss}	Output Capacitance			60		pF
C_{rss}	Reverse Transfer Capacitance			4		pF
E_{oss}	C_{oss} Stored Energy			24		μJ
$C_{O(ER)}$	Effective Output Capacitance, Energy Related	V_{GS}=0V, 0V < V_{DS} < 800V		76		pF
$C_{O(TR)}$	Effective Output Capacitance, Time Related	V_{GS}=0V, 0V < V_{DS} < 800V		110		pF
$R_{G(int)}$	Internal Gate Resistance	f=1MHz, V_{AC}=25mV		3.5		Ω

Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_{GS}	Gate to Source Charge	V_{DS} =800V I_D =20A V_{GS}=-4/+18V		15		nC
Q_{GD}	Gate to Drain Charge			26		nC
Q_G	Total Gate Charge			46		nC

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-On Delay Time	V_{DC}=800V, V_{GS}=-4/18V I_D=20A, $R_{G(ext)}$=2.2Ω L_σ=50nH, T_j=25°C FWD [2]: body diode at V_{GS}=-4V Inductive Load Eon includes diode reverse recovery		9		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn-Off Delay Time			21		ns
t_f	Fall Time			7		ns
E_{on}	Turn-On Energy (Body Diode FWD)			230		uJ
E_{off}	Turn-Off Energy (Body Diode FWD)			30		uJ
E_{on}	Turn-On Energy (SiC Diode FWD)	V_{DC}=800V, V_{GS}=-4/18V I_D=20A, $R_{G(ext)}$=2.2Ω L_σ=50nH, T_j=25°C FWD [2]: B2D10120H1		180		uJ
E_{off}	Turn-Off Energy (SiC Diode FWD)			40		uJ
$t_{d(on)}$	Turn-On Delay Time	V_{DC}=800V, V_{GS}=-4/18V I_D=20A, $R_{G(ext)}$=2.2Ω L_σ=50nH, T_j=175°C FWD [2]: body diode at V_{GS}=-4V Inductive Load Eon includes diode reverse recovery		9		ns
t_r	Rise Time			19		ns
$t_{d(off)}$	Turn-Off Delay Time			25		ns
t_f	Fall Time			9		ns
E_{on}	Turn-On Energy (Body Diode FWD)			370		uJ
E_{off}	Turn-Off Energy (Body Diode FWD)			30		uJ
E_{on}	Turn-On Energy (SiC Diode FWD)	V_{DC}=800V, V_{GS}=-4/18V I_D=20A, $R_{G(ext)}$=2.2Ω L_σ=50nH, T_j=175°C FWD [2]: B2D10120H1		160		uJ
E_{off}	Turn-Off Energy (SiC Diode FWD)			40		uJ

2) Note: FWD: Freewheeling diode

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{SD}	Diode Forward Voltage	V_{GS}=-4V, I_{SD}=10A, T_j=25°C		4.6		V
		V_{GS}=-4V, I_{SD}=10A, T_j=175°C		3.9		
I_{SD}	Continuous Diode Forward Current	V_{GS}=-4V, T_C=25°C			32	A
$I_{SD,pulse}$	Pulse Diode Current	V_{GS}=-4V, pulse width t_p limited by T_{jmax}		80		A
t_{rr}	Reverse Recovery Time	V_{DC}=800V, I_{SD}=20A -di$_F$/dt=2500A/μs T_j=25°C		11		ns
Q_{rr}	Reverse Recovery Charge			110		nC
I_{rrm}	Peak Reverse Recovery Current			16		A
t_{rr}	Reverse Recovery Time	V_{DC}=800V, I_{SD}=20A -di$_F$/dt=3000A/μs T_j=175°C		25		ns
Q_{rr}	Reverse Recovery Charge			470		nC
I_{rrm}	Peak Reverse Recovery Current			29		A

Typical Performance

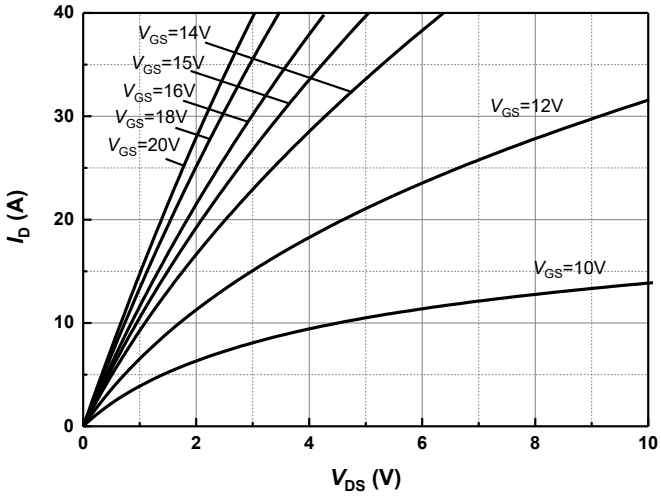


Figure 1 Typical Forward Output Characteristics at T_j=25°C

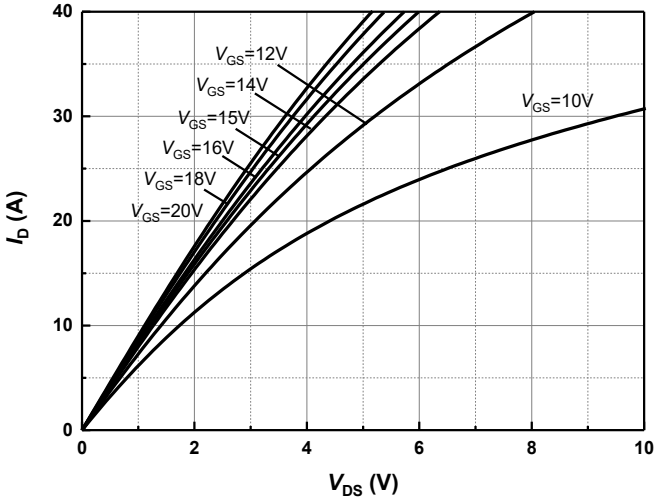


Figure 2 Typical Forward Output Characteristicsat T_j=175°C

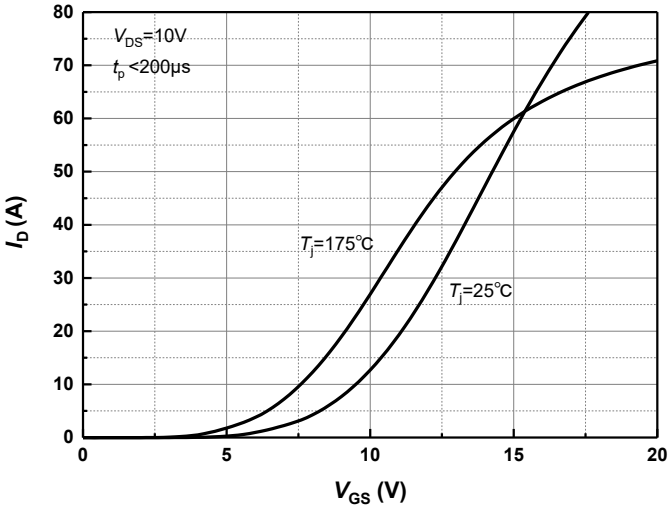


Figure 3 Transfer Characteristics for Various Temperature

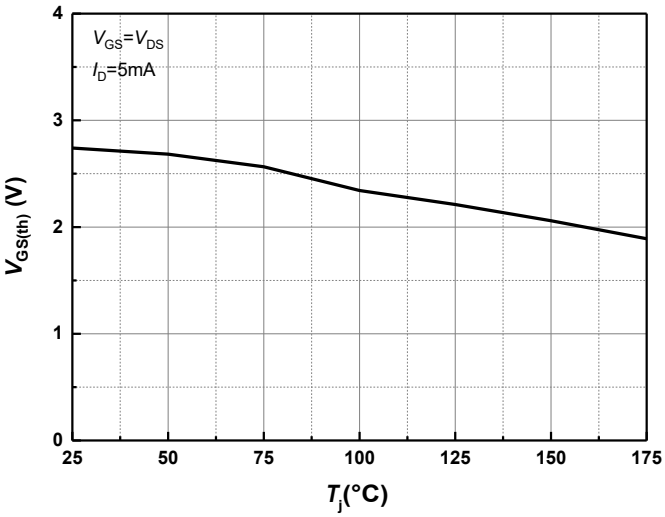


Figure 4 Threshold Voltage for Various Temperature

Typical Performance

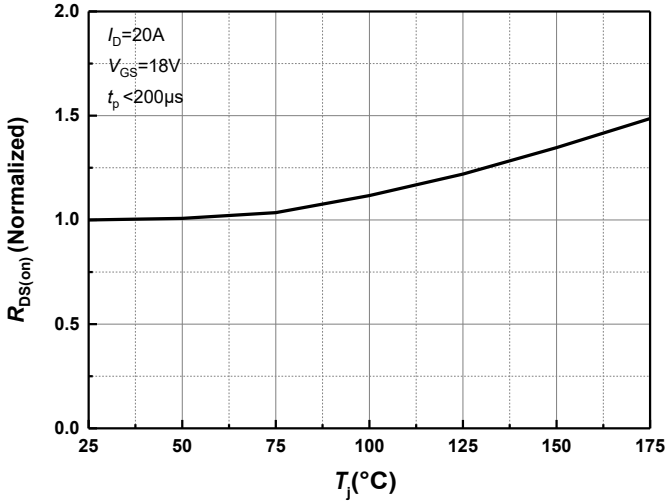


Figure 5 Normalized On-Resistance for Various Temperature

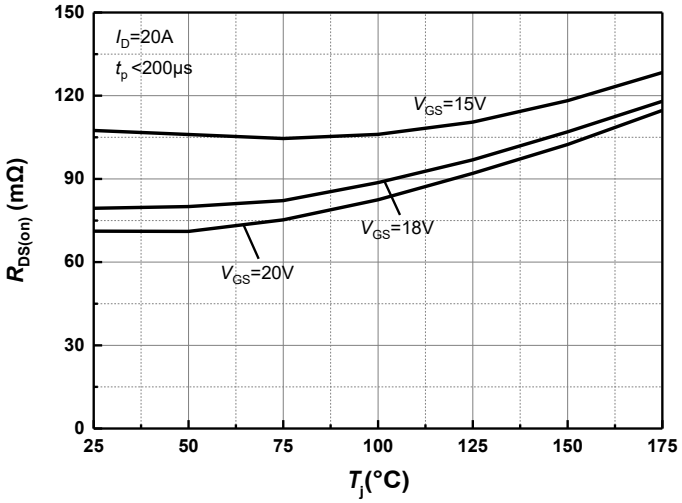


Figure 6 On-Resistance vs. Temperature for Various Gate-Source Voltage

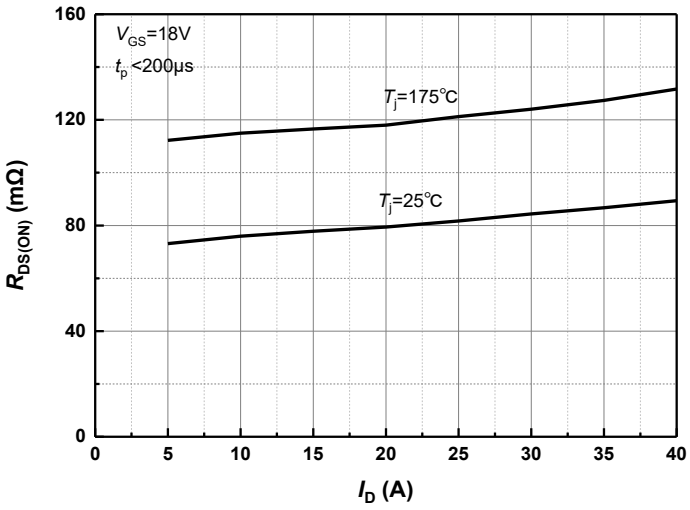


Figure 7 On-Resistance vs. Drain Current for Various Temperature

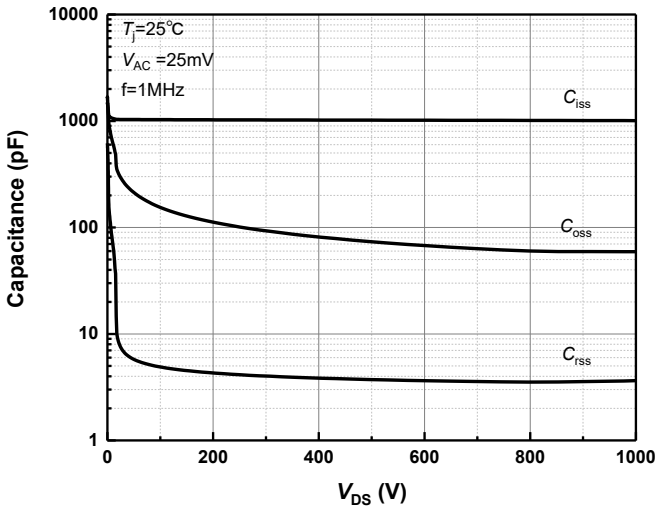


Figure 8 Capacitance vs. Drain-Source Voltage (0 - 1000V)

Typical Performance

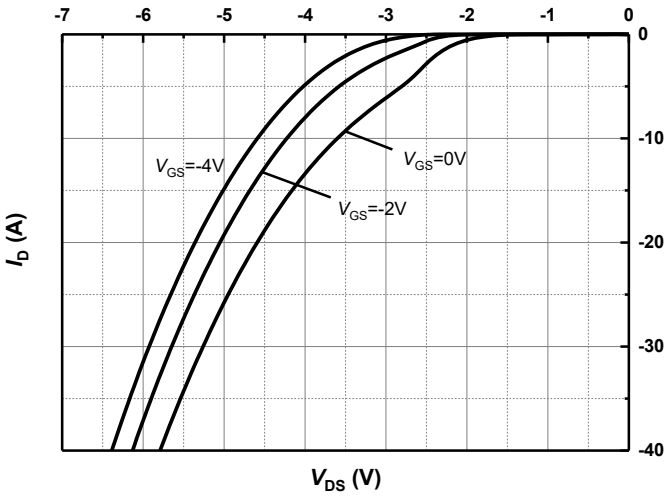


Figure 9 Body Diode Characteristics at T_j=25°C

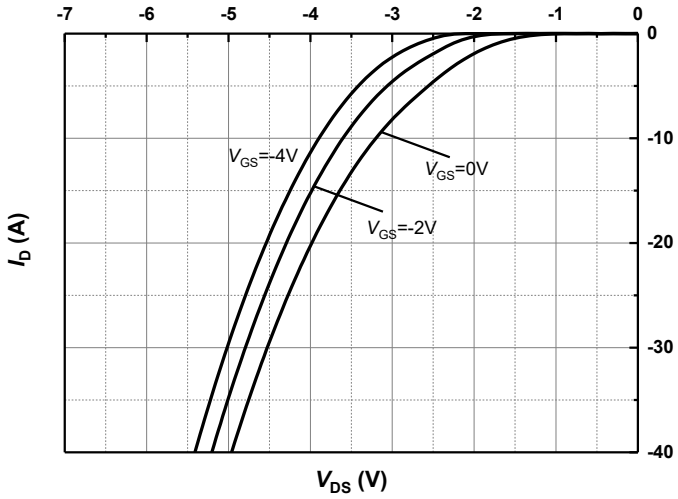


Figure 10 Body Diode Characteristics at T_j=175°C

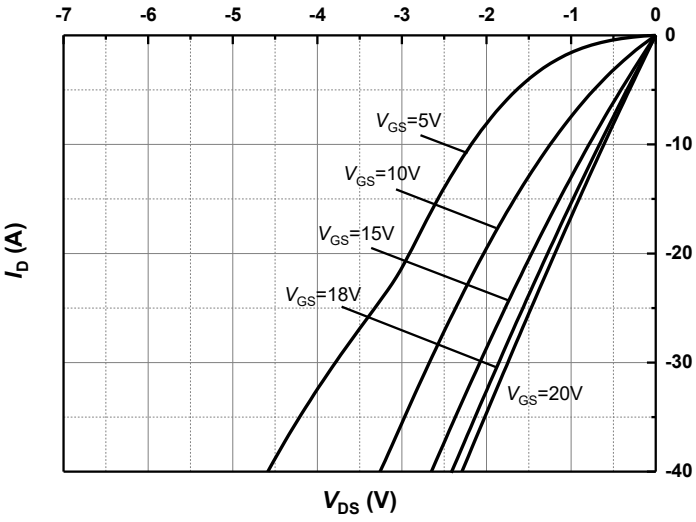


Figure 11 3rd Quadrant Characteristics at T_j=25°C

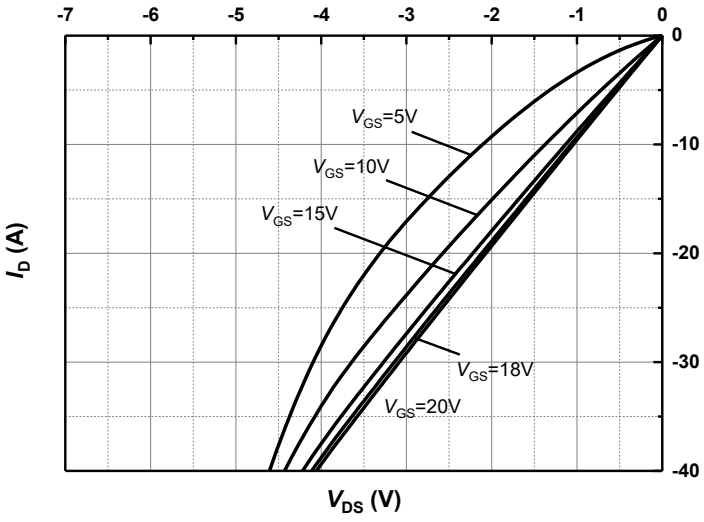


Figure 12 3rd Quadrant Characteristics at T_j=175°C

Typical Performance

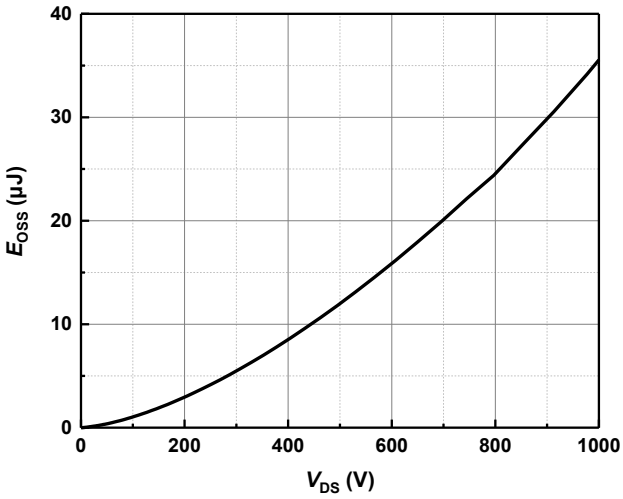


Figure 13 Output Capacitor stored Energy

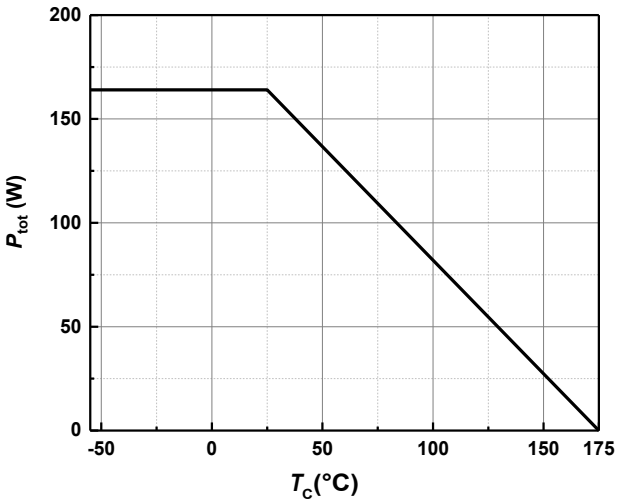


Figure 14 Maximum Power Dissipation Derating vs. Case Temperature

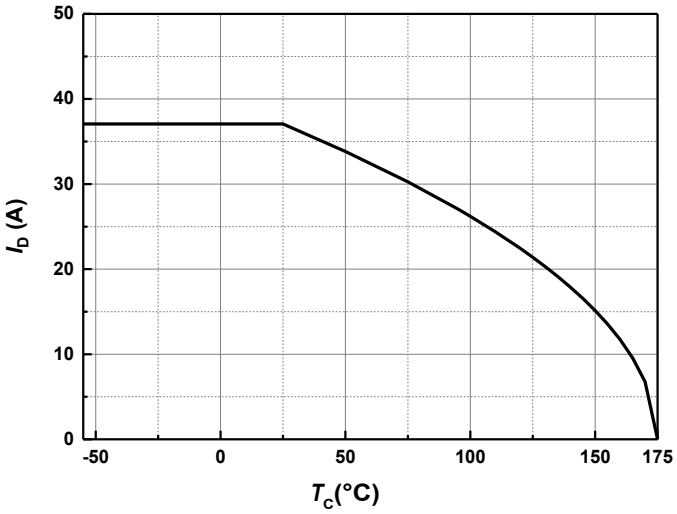


Figure 15 Continuous Drain Current Derating vs. Case Temperature

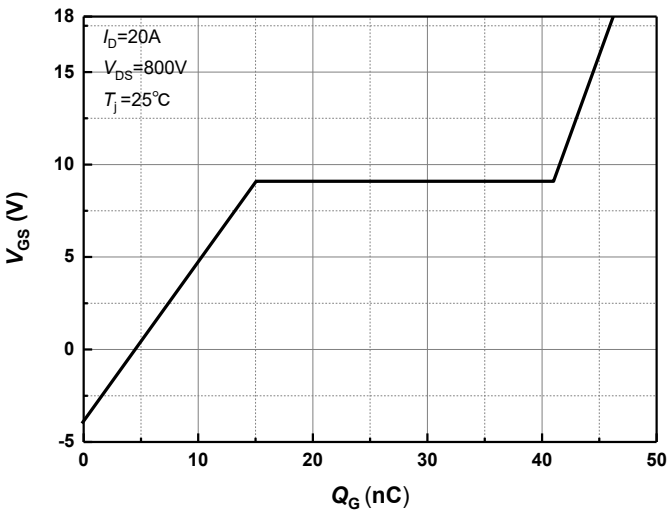


Figure 16 Gate Charge Characteristics

Typical Performance

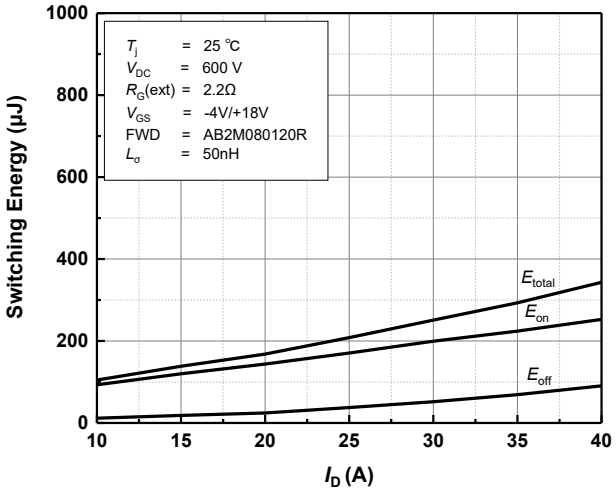


Figure 17 Clamped Inductive Switching Energy vs. Drain Current (V_{DC} =600V) at T_j=25°C

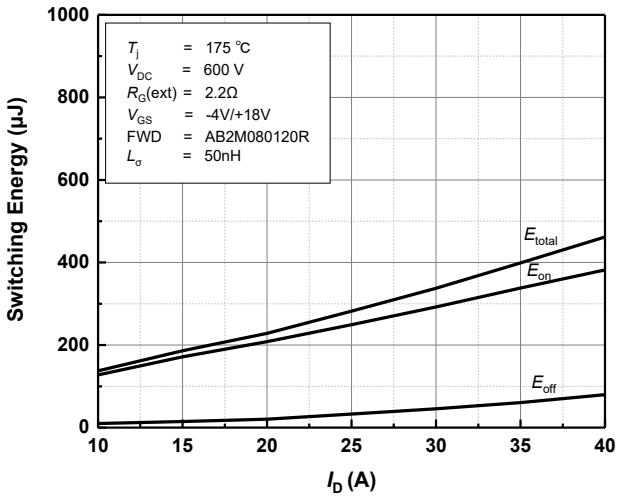


Figure 18 Clamped Inductive Switching Energy vs. Drain Current (V_{DC} =600V) at T_j=175°C

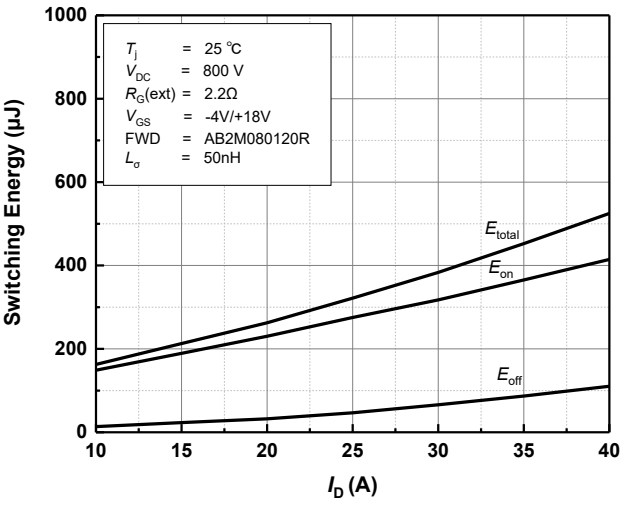


Figure 19 Clamped Inductive Switching Energy vs. Drain Current (V_{DC} =800V) at T_j=25°C

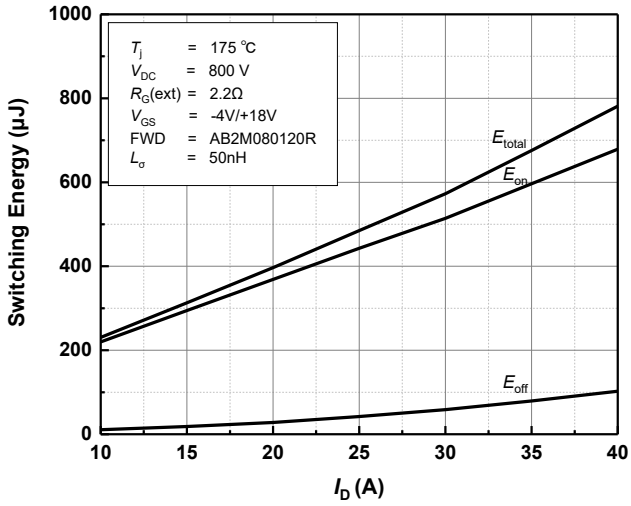


Figure 20 Clamped Inductive Switching Energy vs. Drain Current (V_{DC} =800V) at T_j=175°C

Typical Performance

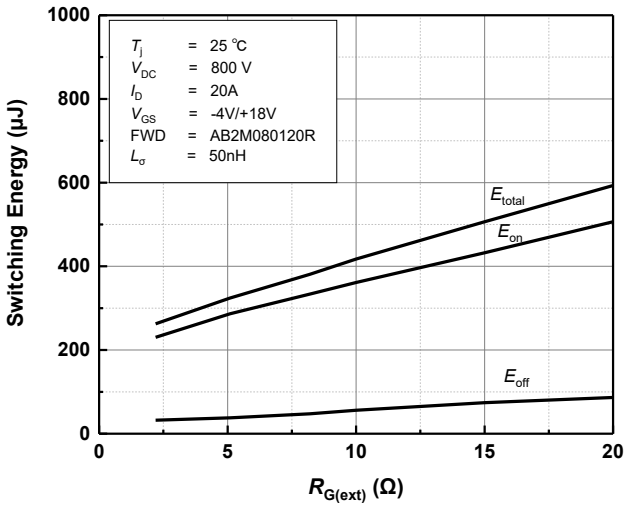


Figure 21 Clamped Inductive Switching Energy vs. External Gate Resistance at T_j=25°C

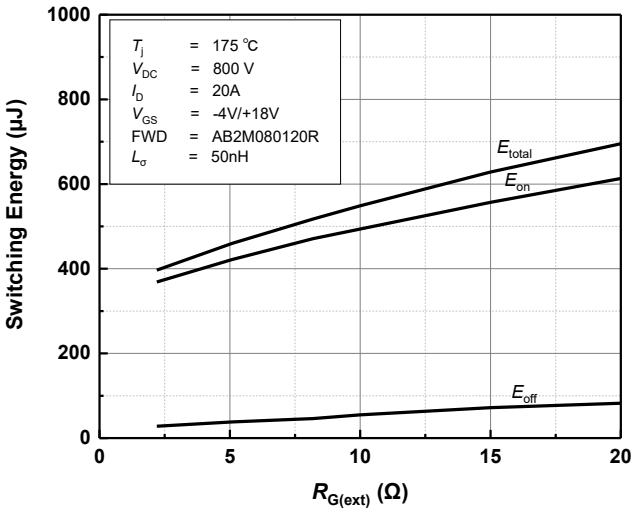


Figure 22 Clamped Inductive Switching Energy vs. External Gate Resistance at T_j=175°C

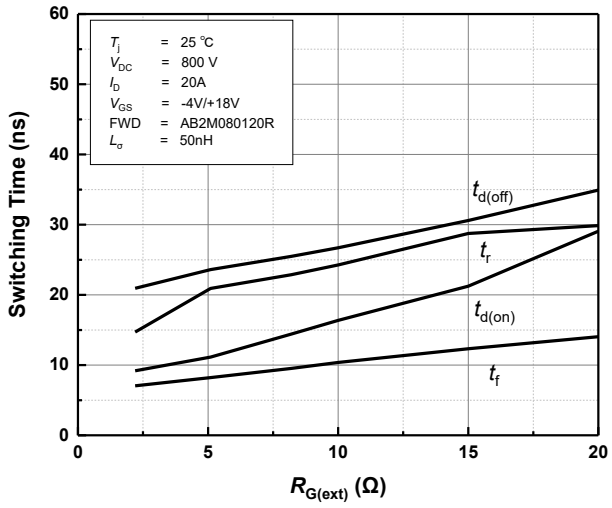


Figure 23 Clamped Inductive Switching Time vs. External Gate Resistance at T_j=25°C

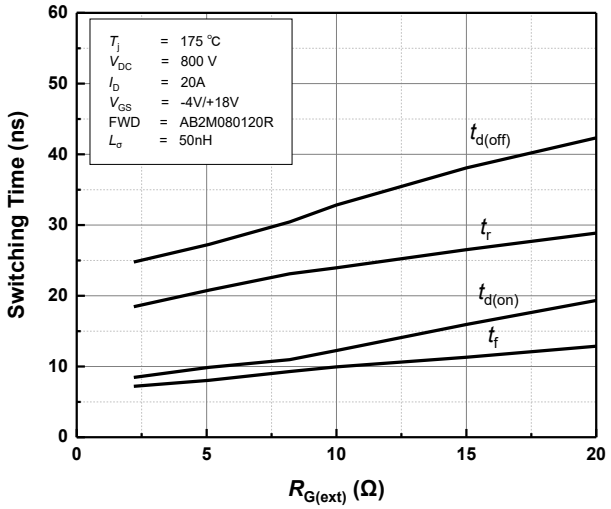


Figure 24 Clamped Inductive Switching Time vs. External Gate Resistance at T_j=175°C

Typical Performance

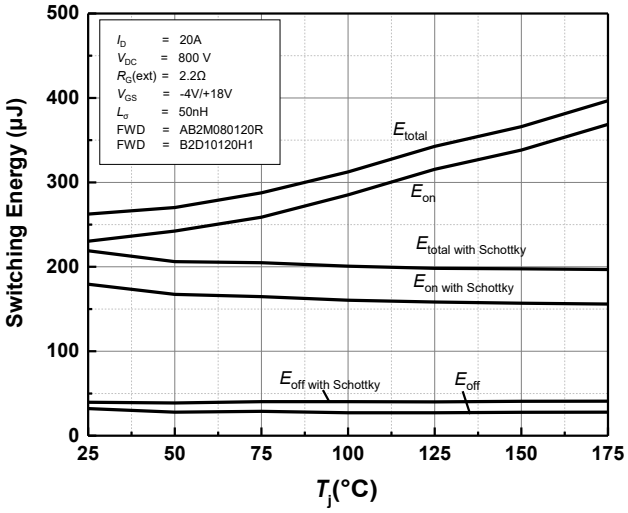


Figure 25 Clamped Inductive Switching Energy vs. Temperature

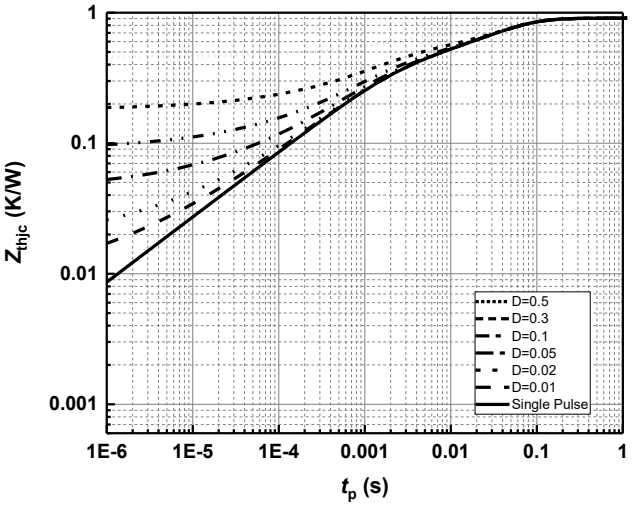


Figure 26 Transient Thermal Impedance (Junction - Case)

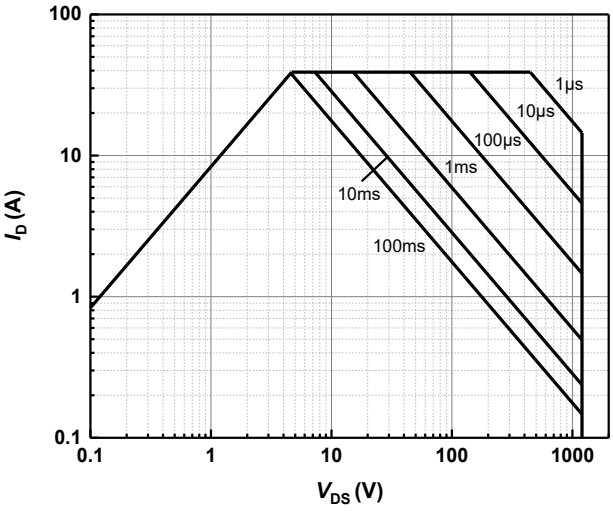
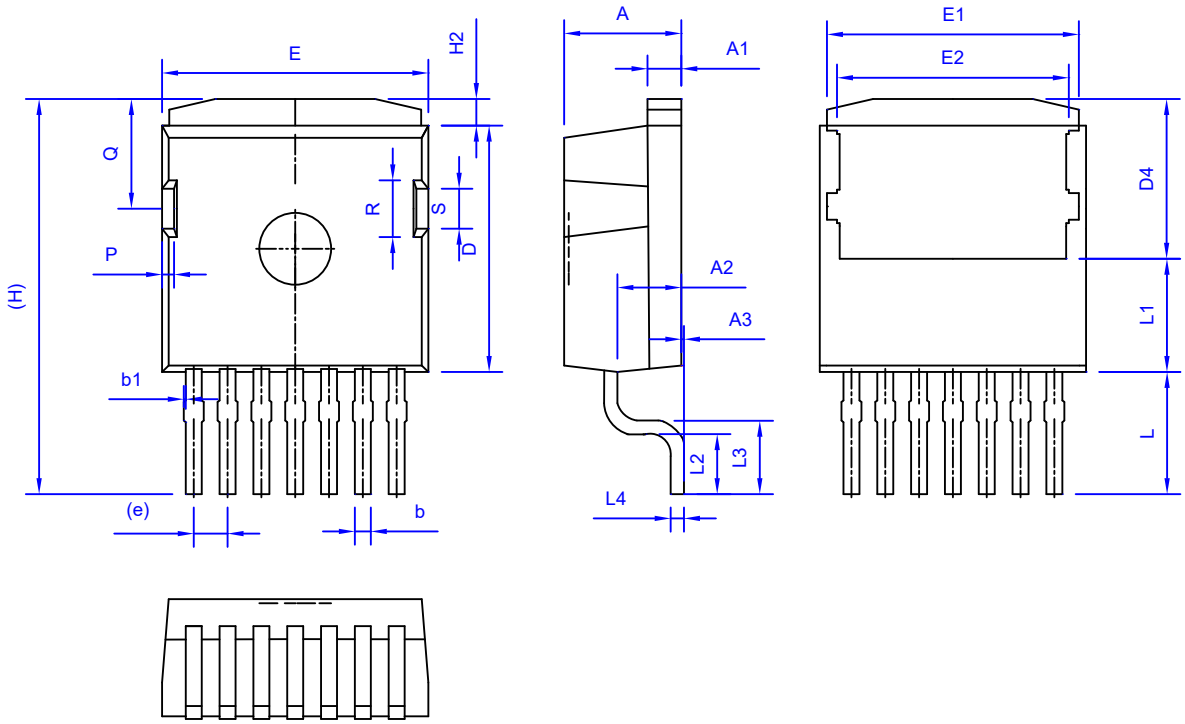


Figure 27 Forward Biased Safe Operating Area

Package Dimensions



SYMBOL	mm		
	MIN	NOM	MAX
A	4.30	4.43	4.56
A1	1.17	1.27	1.40
A2	2.30	2.40	2.50
A3	0.00	0.13	0.25
b	0.50	0.60	0.70
b1	0.00	0.80	0.15
D	9.05	9.25	9.45
D4	5.90	6.00	6.10
E	9.80	10.00	10.20
E1	9.36	9.46	9.56
E2	8.40	8.50	8.60
e		1.27BSC	
H	14.00	15.00	16.00
H2	0.70	1.00	1.30
L	4.20	4.70	5.20
L1		4.250REF	
L2	1.70	2.00	2.30
L3		2.700REF	
L4	0.40	0.50	0.60
P	0.35	0.45	0.55
Q	4.02	4.12	4.22
R	2.03	2.13	2.23
S	1.40	1.50	1.60

Revision History

Document Version	Date of Release	Description of Changes
Rev. 0.0	2024-04-02	Draft datasheet created.
Rev. 0.1	2024-07-12	Updated.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest BASiC Semiconductor Office

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